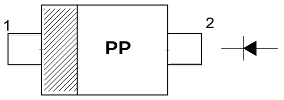
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

For super-high speed switching and
wave detection circuit applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



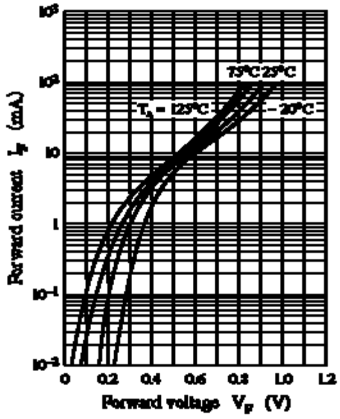
Top View
Marking Code: **"PP"**
Simplified outline SOD-323 and symbol

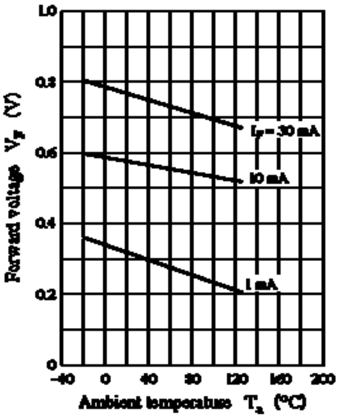
Absolute Maximum Ratings (T_a = 25 °C)

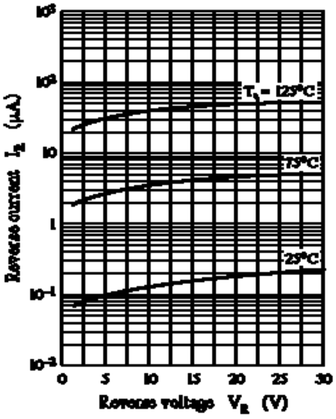
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	30	V
Reverse Voltage	V_R	30	V
Forward Current	I_F	30	mA
Peak Forward Current	I_{FM}	150	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

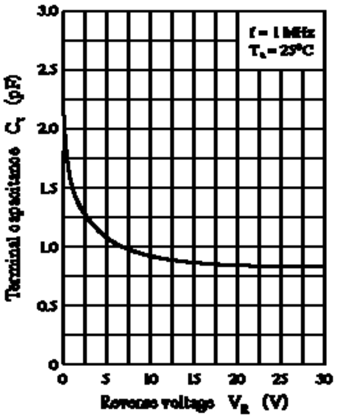
Characteristics at T_a = 25 °C

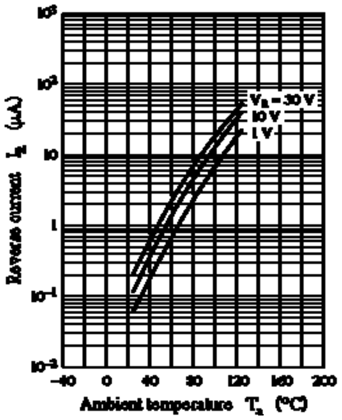
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA at I_F = 30 mA	V_F	- -	0.4 1	V
Reverse Current at V_R = 30 V	I_R	-	0.3	µA
Terminal Capacitance at V_R = 1 V, f = 1 MHz	C_T	1.5	-	pF
Reverse Recovery Time at $I_F = I_R$ = 10 mA, I_{rr} = 1 mA, R_L = 100 Ω	t_{rr}	1	-	ns
Detection Efficiency at V_{in} = 3 $V_{(peak)}$, f = 30 MHz, R_L = 3.9 KΩ, C_L = 10 pF	η	65	-	%


I_F — V_F


V_F — T_a


I_R — V_R


C_t — V_R


I_R — T_a